

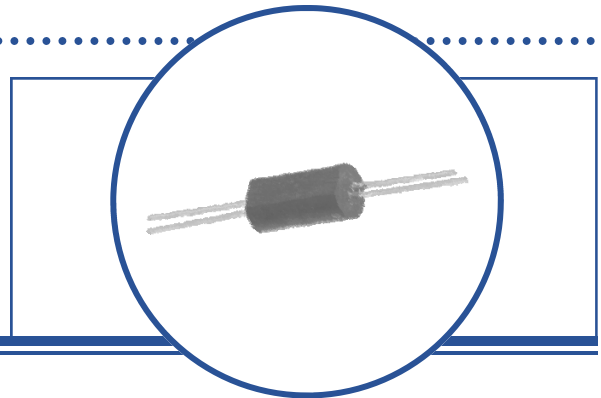
Optically Coupled Isolator

OPI110, OPI1264 Series



Features:

- 10 kV electrical isolation
- Choice of phototransistor
- Low-cost plastic housing
- UL recognized File No. E58730*



Description:

Each Optoisolator in this data sheet contains an infrared Light Emitting Diode (LED) and a NPN silicon Photosensor. The **OPI110** and **OPI1264** devices have 890 nm Light Emitting Diode (LED) and NPN phototransistor sensor. The devices are sealed in a precast opaque housing with an optically transmissive path between the LED and the photosensor.

The Optoisolators in this data sheet are UL approved under E 58730.

This series is designed for transmission of information between one power supply voltage and another where the potentials during surge conditions are not greater than the guaranteed isolation voltage.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- High voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment
- Office equipment

Ordering Information							
Part Number	LED Peak Wavelength	Sensor	Isolation Voltage (,000)	CTR Min / Max	I _F (mA) Typ / Max	V _{CE} (Volts) Max	Lead Length / Spacing
OPI110	890 nm	Transistor	10	12.5 / NA	10 / 40	30	0.50" / 0.55"
OPI110A				25 / NA			
OPI110B				50 / 125			
OPI110C				100 / NA			
OPI1264		Transistor		12.5 / NA	10 / 40		
OPI1264A				25 / NA			
OPI1264B				50 / 125			
OPI1264C				100 / NA			



RoHS

OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage Temperature ⁽¹⁾⁽²⁾	-40° C to +100° C
Operating Temperature	-40° C to +85° C
Input-to-Output Isolation Voltage	± 10 kVDC
Lead Soldering Temperature (1/16" (1.6 mm) from case for 5 seconds with soldering iron) ⁽³⁾	260° C

Input Diode

Forward DC Current ⁽⁴⁾	40 mA
Reverse DC Voltage	2 V
Power Dissipation ⁽⁵⁾	50 mW

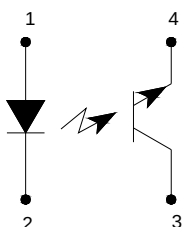
Output Photosensor

Collector-Emitter Voltage OPI110, OPI1264	30 15
Emitter-Collector Voltage	5
Power Dissipation ⁽⁶⁾	100 mW

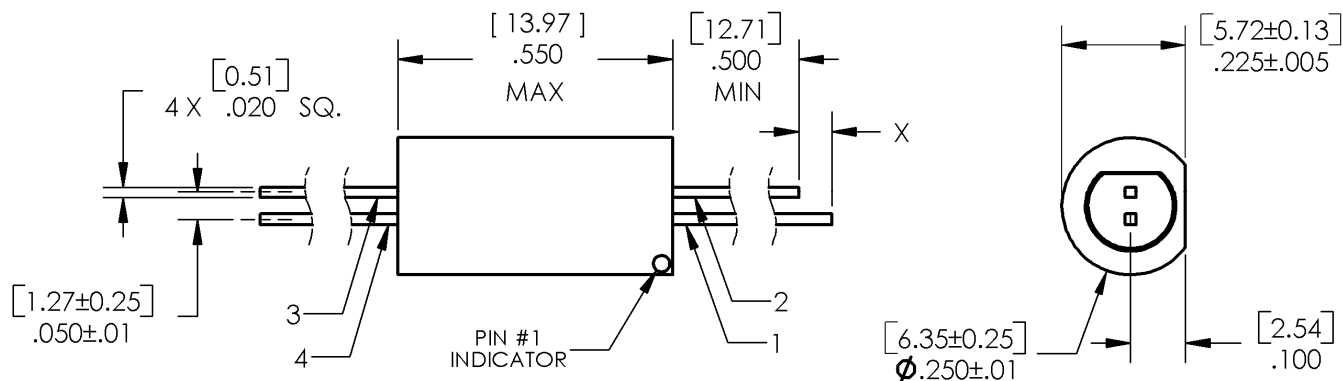
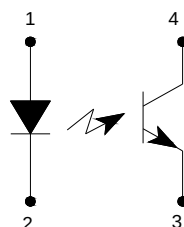
Notes:

- (1) Measured with input and output leads shorted. Typical input/output capacitance is 0.06 pF.
- (2) UL recognition is for 3500 VAC for one minute.
- (3) RMA flux is recommended. The duration can be extended to 10 seconds maximum when flow soldering.
- (4) Derate linearly 0.67 mA/°C above 25°C.
- (5) Derate linearly 0.83 mA/°C above 25°C.
- (6) Derate linearly 1.67 mW/°C above 25°C.

OPI110



OPI1264



DIMENSIONS ARE IN: [MILLIMETERS]
INCHES

OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
--------	-----------	-----	-----	-----	-------	-----------------

Input Diode (See OP265 for additional information - for reference only)

V_F	Forward Voltage	-	-	1.6	V	$I_F = 20\text{ mA}$
I_R	Reverse Current	-	-	100	μA	$V_R = 2\text{ V}$

Output Photosensor (See OP505 for additional information - for reference only)

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage OPI110, OPI1264	30	-	-	V	$I_C = 100\text{ }\mu\text{A}$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage OPI110 OPI1264	5 -	- -	- -	V	$I_E = 100\text{ }\mu\text{A}$, $I_F = 0$ $I_E = 100\text{ }\mu\text{A}$
I_{CEO}	Collector-Emitter Dark Current OPI110, OPI1264	-	-	100	nA	$V_{CE} = 15\text{ V}$, $E_E = 0$

Coupled

$I_{C(ON)}$	Coupled "ON" Current OPI110, OPI1264	1.25	-	44	mA	$I_F = 10\text{ mA}$ $V_{CE} = 5\text{ V}$
I_C/I_F	DC Current Transfer Ratio OPI110, OPI1264 OPI110A, OPI1264A OPI110B, OPI1264B OPI110C, OPI1264C	12.5 25.0 50.0 100.0	- - - -	- - 125 -	%	$I_F = 10\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_F = 10\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_F = 10\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_F = 10\text{ mA}$, $V_{CE} = 5\text{ V}$
$V_{CE(SAT)}$	Collector Saturation Voltage OPI110, OPI1264	-	-	0.4	V	$I_F = 10\text{ mA}$, $I_C = 1.6\text{ mA}$
I_{CEO}	Collector-Emitter Dark Current OPI110, OPI1264	-	-	200	nA	$V_{CE} = 20\text{ V}$, $I_F = 0$
V_{ISO}	Isolation Voltage	10	-	-	kVDC	See Note 1.

Notes:

(1) Measured with input and output leads shorted. Typical input/output capacitance is 0.06 pF.

OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9